

L Number	Hits	Search Text	DB	Time stamp
1	25	(second adj stop) same stack same (trench or opening or contact)	USPAT; EPO; JPO; IBM_TDB	2003/05/08 14:14
2	555	(second adj stop) and stack and (trench or opening or contact)	USPAT; EPO; JPO; IBM_TDB	2003/05/08 14:16
3	849	(second adj stop) and (stack or stacked or stacking) and (trench or opening or contact)	USPAT; EPO; JPO; IBM_TDB	2003/05/08 14:20
5	14	(second adj stop) and (stack or stacked or stacking) and (trench or opening or contact) and etch\$3 and polish\$3	USPAT; EPO; JPO; IBM_TDB	2003/05/08 14:34
6	448	("silicon oxide" or SiO) and ("silicon nitride" or SiN) and "stop layer" and (stack or stacked or stacking) and (trench or opening or contact) and etch\$3 and polish\$3	USPAT; EPO; JPO; IBM_TDB	2003/05/08 15:53
7	448	("silicon oxide" or SiO) and ("silicon nitride" or SiN) and "stop layer" and (stack or stacked or stacking) and (trench or opening or contact) and etch\$3 and polish\$3) and etch\$3	USPAT; EPO; JPO; IBM_TDB	2003/05/08 14:38
8	12718	(dielectric or insulating) same trench	USPAT; EPO; JPO; IBM_TDB	2003/05/08 14:40
9	237	((("silicon oxide" or SiO) and ("silicon nitride" or SiN) and "stop layer" and (stack or stacked or stacking) and (trench or opening or contact) and etch\$3 and polish\$3) and etch\$3) and ((dielectric or insulating) same trench)	USPAT; EPO; JPO; IBM_TDB	2003/05/08 14:40
10	464	("silicon oxide" or SiO) and ("silicon nitride" or SiN) and ("stop layer" or "polish stop") and (stack or stacked or stacking) and (trench or opening or contact) and etch\$3 and polish\$3	USPAT; EPO; JPO; IBM_TDB	2003/05/08 16:06
11	5815	"shallow trench isolation" or STI	USPAT; EPO; JPO; IBM_TDB	2003/05/08 16:07
12	138	(("silicon oxide" or SiO) and ("silicon nitride" or SiN) and ("stop layer" or "polish stop") and (stack or stacked or stacking) and (trench or opening or contact) and etch\$3 and polish\$3) and ("shallow trench isolation" or STI)	USPAT; EPO; JPO; IBM_TDB	2003/05/08 16:11
13	1718	((438/424) or (438/221) or (438/244) or (438/296) or (438/691)).CCLS.	USPAT; EPO; JPO; IBM_TDB	2003/05/08 16:14
14	25	((("silicon oxide" or SiO) and ("silicon nitride" or SiN) and ("stop layer" or "polish stop") and (stack or stacked or stacking) and (trench or opening or contact) and etch\$3 and polish\$3) and (((438/424) or (438/221) or (438/244) or (438/296) or (438/691)).CCLS.)	USPAT; EPO; JPO; IBM_TDB	2003/05/08 16:14